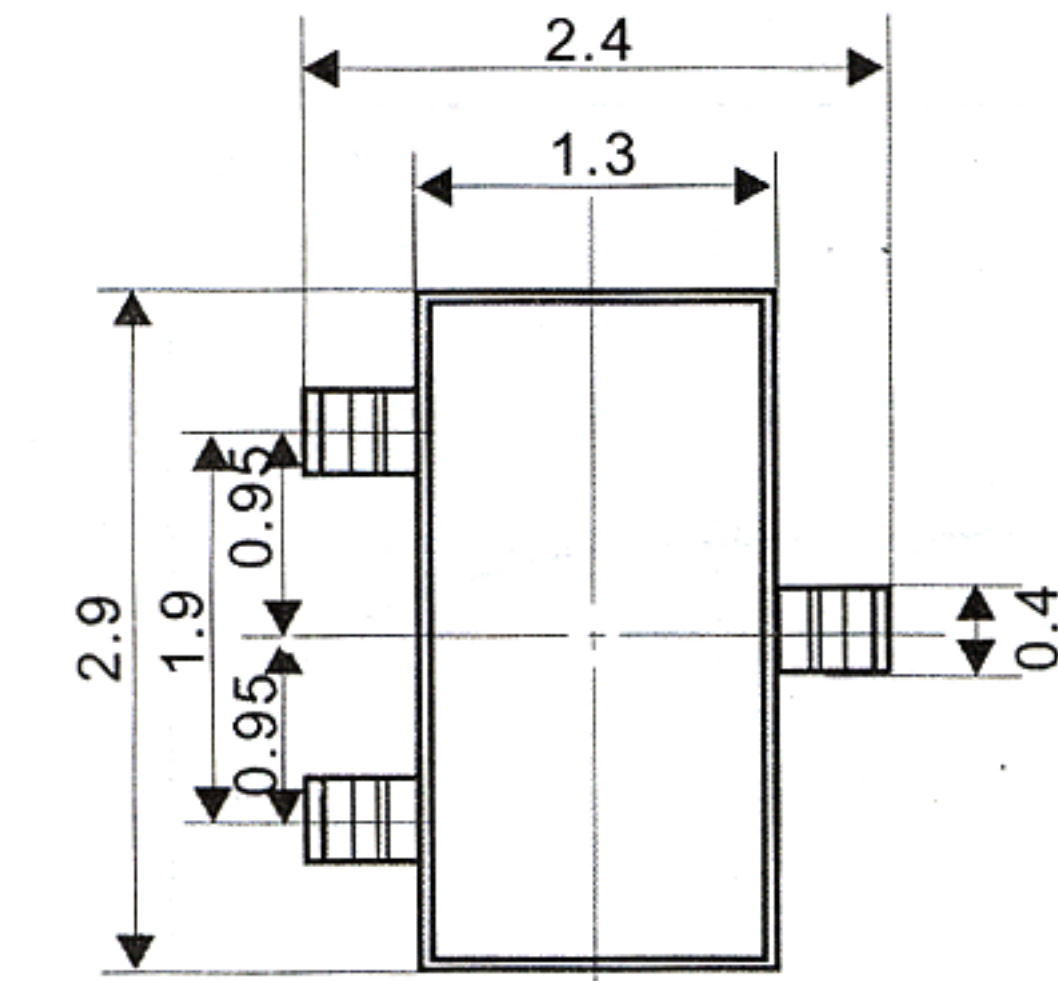
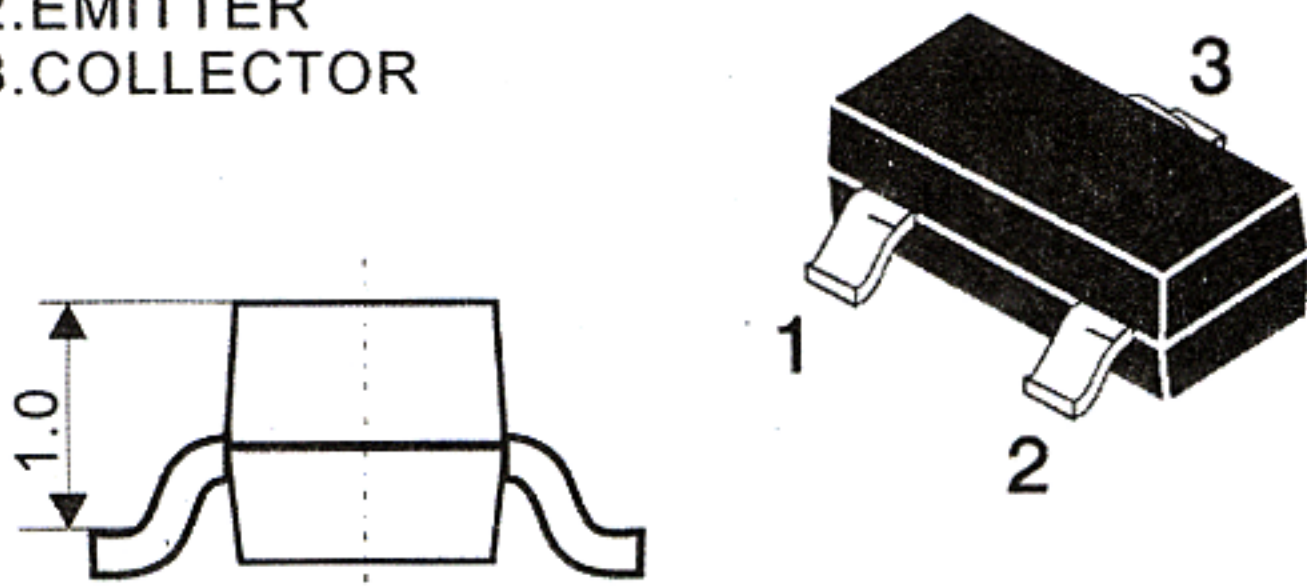


SOT-23 Plastic-Encapsulate Transistors

S8550LT1 TRANSISTOR (PNP)

1. BASE
2. EMITTER
3. COLLECTOR



UNIT: mm

FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -40V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

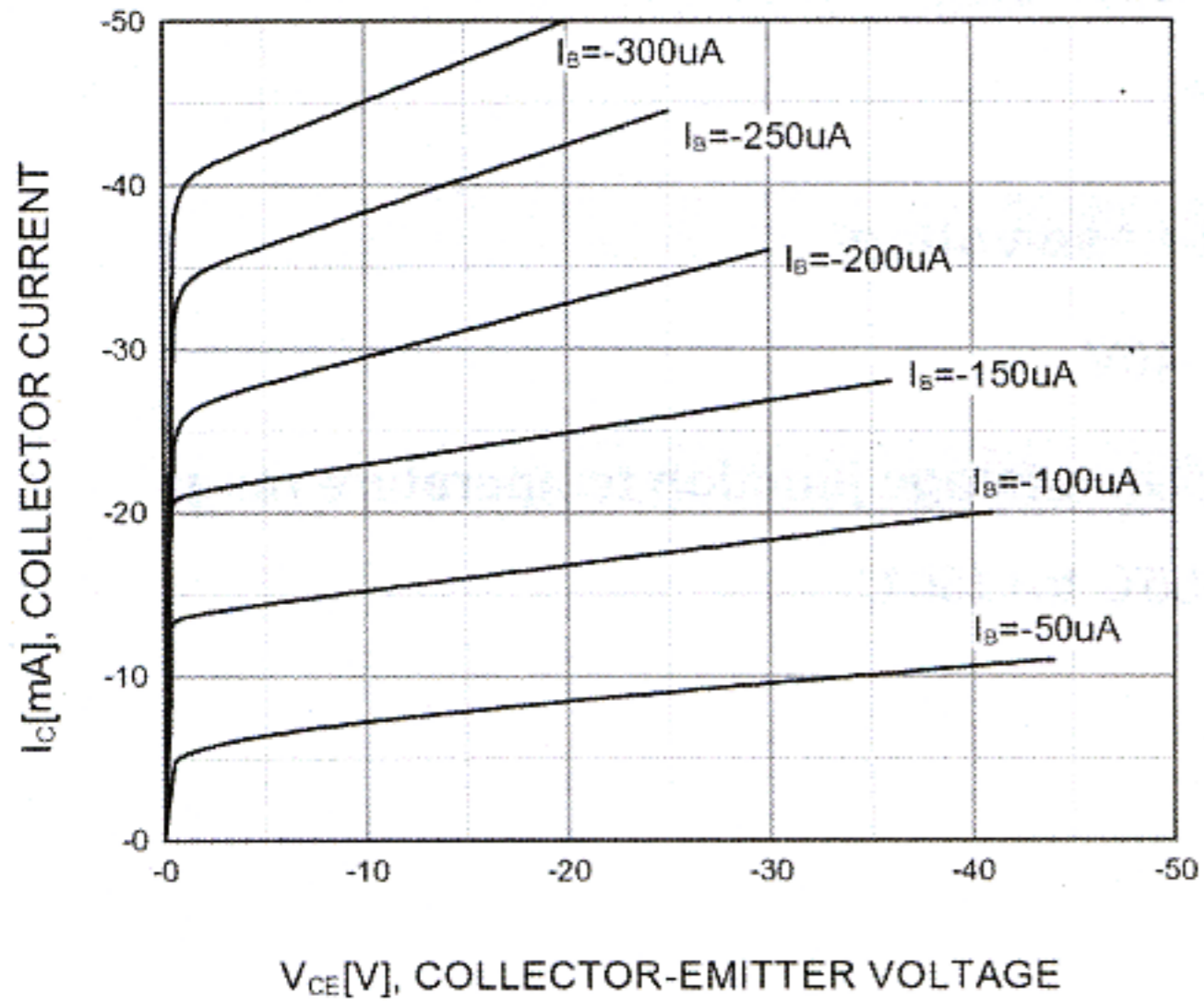
($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-0.1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20V, I_B=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3V, I_C=0mA$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-50mA$	120		350	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-500mA$	50			
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-500mA, I_B=-50mA$			-0.6	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-500mA, I_B=-50mA$			-1.2	V
Base-emitter voltage	V_{BEF}	$I_E=-100mA$			-1.4	V
Transition frequency	f_T	$V_{CE}=-6V, I_C=-20mA, f=30MHz$	150			MHz

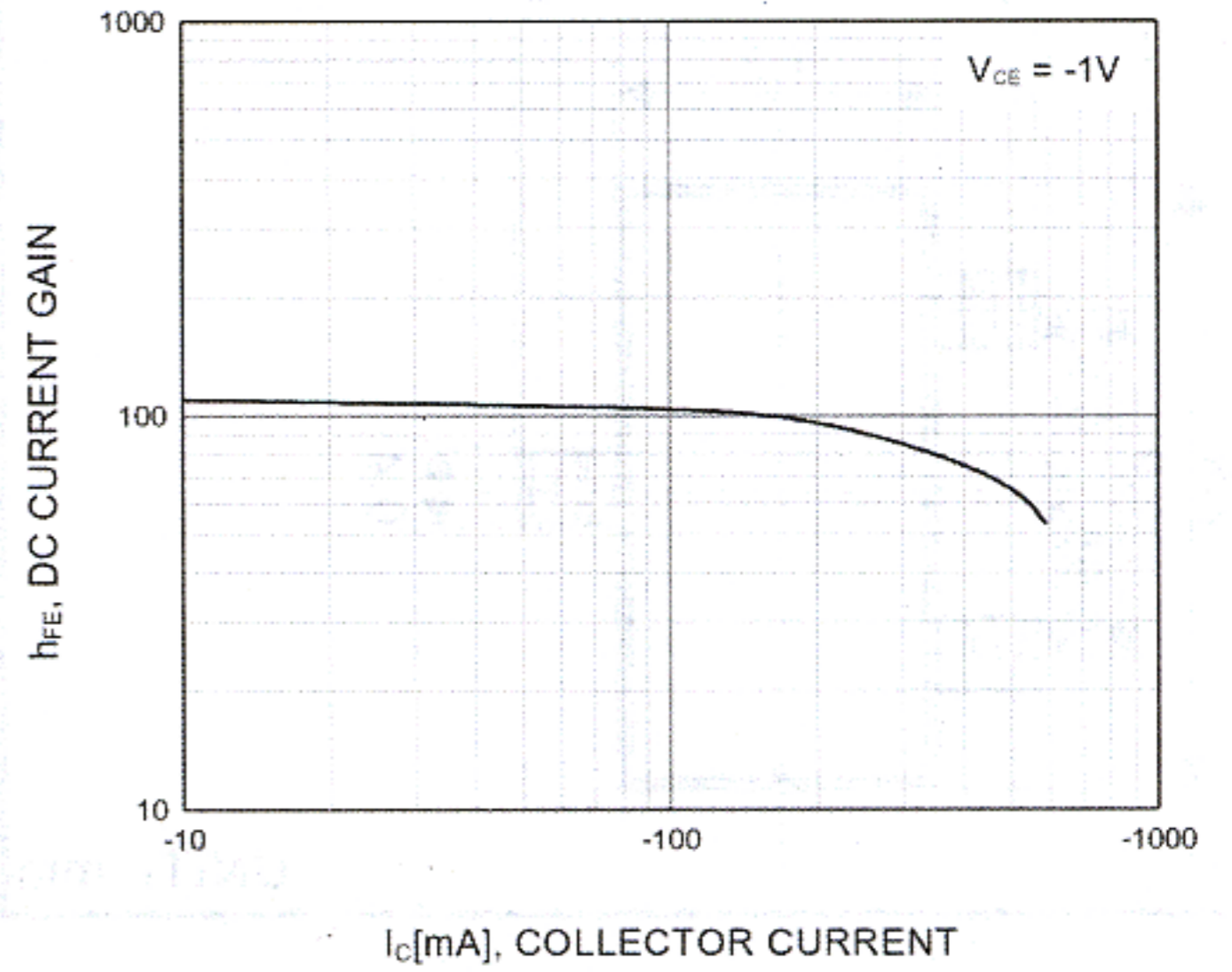
CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	120-200	200-350

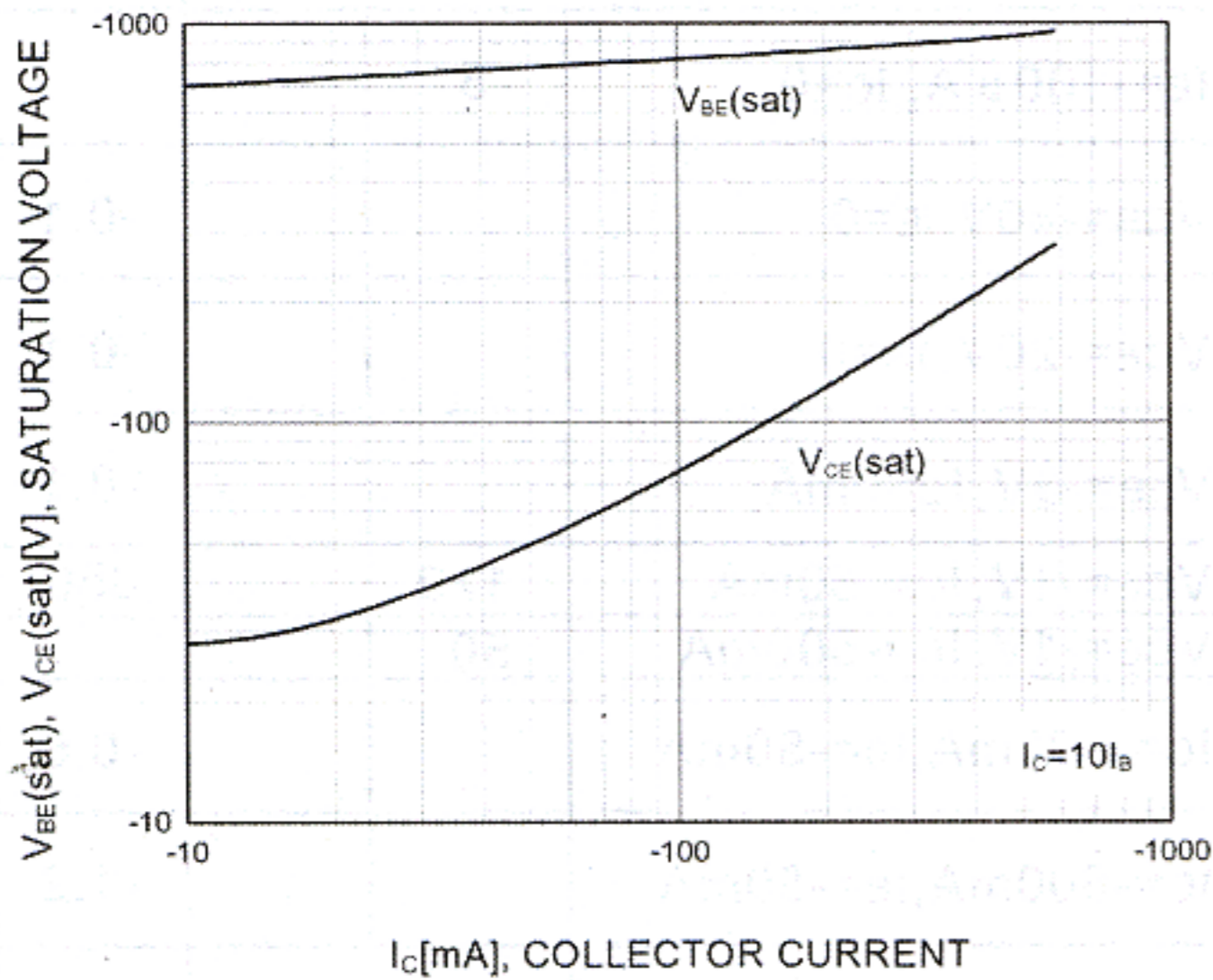
DEVICE MARKING : S8550LT1=2TY



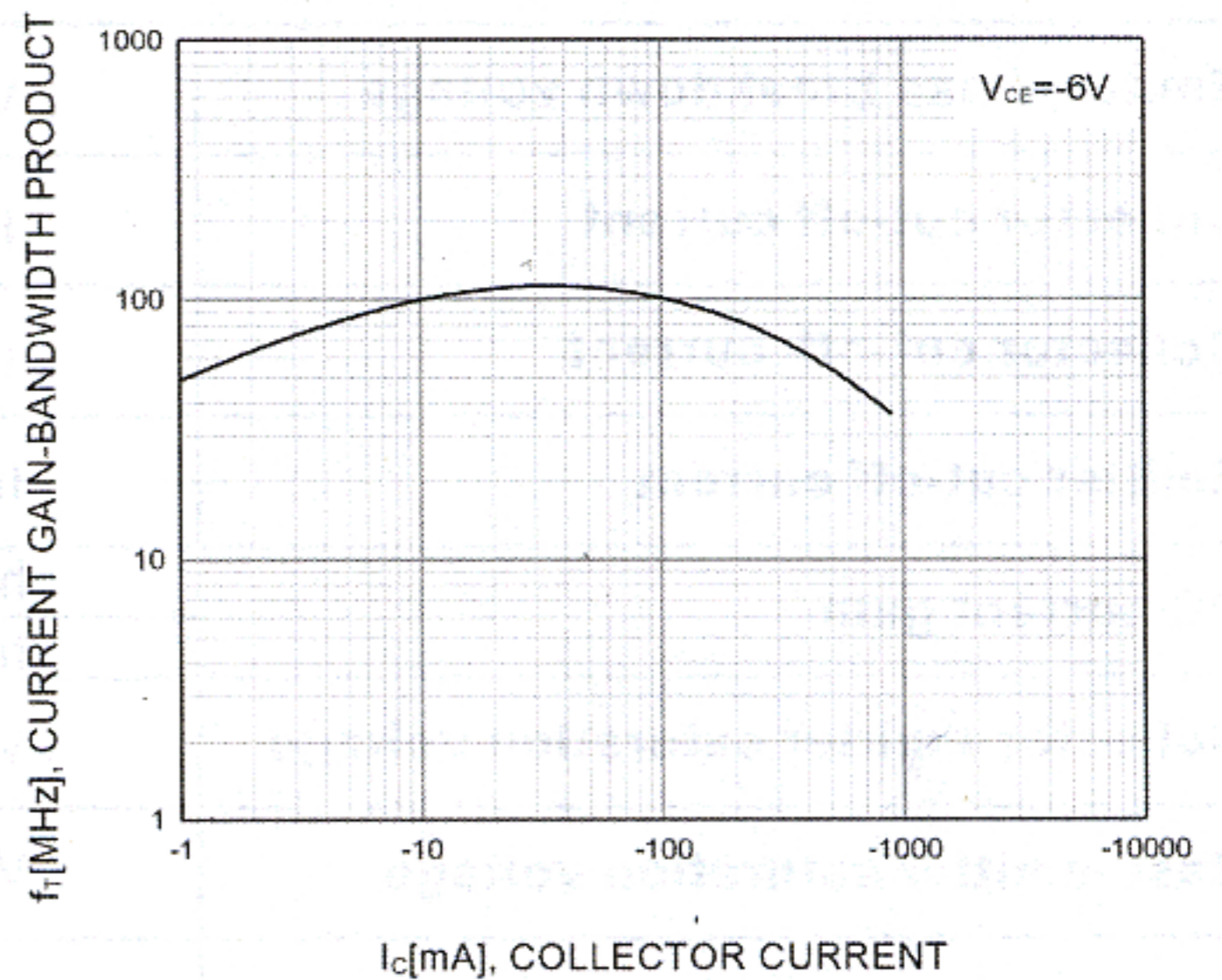
Static Characteristic



DC current Gain



**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Current Gain Bandwidth Product